L Number	Hits	Search Text	DB	Time stamp
1	432	438/96.ccls.	USPAT	2004/09/29
				17:33
3	264	438/97.ccls.	USPAT	2004/09/29
				17:33
	682	438/149.ccls.	USPAT	2004/09/29
4	400	420/4501-		17:33
	100	438/150.ccls.	USPAT	2004/09/29
5	661	438/151.ccls.	USPAT	17:34
	001	436/131.ccis.	USPAI	2004/09/29 17:34
6	641	438/166.ccls.	USPAT	2004/09/29
	04.	430/100.0013.	USPAI	17:34
7	480	438/479.ccls.	USPAT	2004/09/29
	100	430/4/3/66/3/	USFAI	17:34
8	251	438/482.ccls.	USPAT	2004/09/29
		100/102100101	JOHAI	17:34
9	385	438/486.ccls.	USPAT	2004/09/29
			JOIAI	17:34
10	347	438/487.ccls.	USPAT	2004/09/29
				17:34
11	381	438/488.ccls.	USPAT	2004/09/29
				17:34
12	83	438/491.ccls.	USPAT	2004/09/29
			ŀ	17:35
13	75	lee-seok\$.in.	USPAT	2004/09/29
				17:35
14	91	lee-seok\$.in.	US-PGPUB	2004/09/29
		·		17:35
15	48	lee-seok\$.in.	EPO; JPO;	2004/09/29
			DERWENT;	17:35
			IBM_TDB	
16	10249	(amorph\$6 and crystal\$9) and (anneal\$6 rta	USPAT	2004/09/29
		rtp rto) and (silicon polysilicon)		17:41
17	. 4160	((amorph\$6 and crystal\$9) and (anneal\$6	USPAT	2004/09/29
		rta rtp rto) and (silicon polysilicon)) and		17:41
		(TFT (thin same transistor))		
18	7700	((amorph\$6 and crystal\$9) and (anneal\$6	USPAT	2004/09/29
		rta rtp rto) and (silicon polysilicon)) and		17:38
19	3406	(amorph\$6 same crystal\$9)		0004/00/00
19	3406	(((amorph\$6 and crystal\$9) and (anneal\$6	USPAT	2004/09/29
		rta rtp rto) and (silicon polysilicon)) and (amorph\$6 same crystal\$9)) and		17:39
		(((amorph\$6 and crystal\$9) and (anneal\$6		
		rta rtp rto) and (silicon polysilicon)) and		
		(TFT (thin same transistor)))		
20	2675	((((amorph\$6 and crystal\$9) and (anneal\$6	USPAT	2004/09/29
		rta rtp rto) and (silicon polysilicon)) and	JOPAI	17:39
		(amorph\$6 same crystal\$9)) and		11103
		(((amorph\$6 and crystal\$9) and (anneal\$6		
		rta rtp rto) and (silicon polysilicon)) and		
		(TFT (thin same transistor)))) and active		

21	2380	(((((amorph\$6 and crystal\$9) and (anneal\$6	USPAT	2004/09/29
		rta rtp rto) and (silicon polysilicon)) and		17:39
		(amorph\$6 same crystal\$9)) and		
		(((amorph\$6 and crystal\$9) and (anneal\$6		
		rta rtp rto) and (silicon polysilicon)) and		
		(TFT (thin same transistor)))) and active)		
		and pattern\$6		
22	170	((((((amorph\$6 and crystal\$9) and	USPAT	2004/09/29
		(anneal\$6 rta rtp rto) and (silicon		17:40
		polysilicon)) and (amorph\$6 same		·
		crystal\$9)) and (((amorph\$6 and crystal\$9)		
		and (anneal\$6 rta rtp rto) and (silicon		
		polysilicon)) and (TFT (thin same		
		transistor)))) and active) and pattern\$6) and		
		(rapid same oxid\$9)		
23	1609	((((((amorph\$6 and crystal\$9) and	USPAT	2004/09/29
		(anneal\$6 rta rtp rto) and (silicon		17:41
		polysilicon)) and (amorph\$6 same		
,		crystal\$9)) and (((amorph\$6 and crystal\$9)		
		and (anneal\$6 rta rtp rto) and (silicon		
		polysilicon)) and (TFT (thin same		
		transistor)))) and active) and pattern\$6) and		
		pixel		
24	3968	(amorph\$6 same crystal\$9) and (anneal\$6	US-PGPUB	2004/09/29
		rta rtp rto) and (silicon polysilicon)		17:42
25	2062	((amorph\$6 same crystal\$9) and (anneal\$6	US-PGPUB	2004/09/29
		rta rtp rto) and (silicon polysilicon)) and		17:42
		(TFT (thin same transistor))		
26	1451	(((amorph\$6 same crystal\$9) and (anneal\$6	US-PGPUB	2004/09/29
		rta rtp rto) and (silicon polysilicon)) and		17:42
		(TFT (thin same transistor))) and pixel		
27	1108	(amorph\$6 same crystal\$9) and (anneal\$6	EPO; JPO;	2004/09/29
		rta rtp rto) and (silicon polysilicon)	DERWENT;	17:42
			IBM_TDB	
28	369	((amorph\$6 same crystal\$9) and (anneal\$6	EPO; JPO;	2004/09/29
		rta rtp rto) and (silicon polysilicon)) and	DERWENT;	17:42
		(TFT (thin same transistor))	IBM TDB	1